FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.196CP1	APPLICATION NO. 09/318,073
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	APPLICANT Zhu, et al.	
(USE SEVERAL SHEETS IF NECESSARY)	FILING DATE May 25, 1999	GROUP 2826

OIPE JC1 JUL 12 2002 PATENT & TRADEMARK OFFICE

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
WS		US 2001/0030886 A1	10/18/01	Thewes, et al.			
WS		US 2001/0050859 A1	12/13/01	Schwarzl			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

MSO-3132.DOC:afa
070802

EXAMINER	DATE CONSIDERED 12/04/2002

EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES	TRANSLATION NO
WM		JP 2000 090658 A	3/31/00	Japan (Abstract)			X	

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WM		Prinz, "Magnetoelectronics", Science Magazine, Vol. 282, Nov. 27, 1998.
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		Lee, Chih-Ling, "A Study of Magnetoresistance Random-Access Memory," date unknown
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EXAMINER	DATE CONSIDERED 10/29/2004

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